



A35076-PCT-USA (070050.2713)  
PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : James S. Im Customer No. : 21003  
Serial No. : 10/525,288 Confirmation No. : 7758  
Filed : 02/16/2005 Group Art Unit : 2813  
Examiner :  
For : Process And System For Laser Crystallization Processing Of Film Regions  
On A Substrate To Provide Substantial Uniformity, And A Structure Of  
Such Film Regions

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

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David Schalk  
Name of Person  
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*David Schalk*  
Signature

March 27, 2006  
Date of Signature

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), applicants bring to the attention of  
the Examiner the document listed on the attached Form PTO-1449 and respectfully request  
that the listed documents be considered by the Examiner and made of record in the above-  
captioned application. Copies of all U.S. Patents and Applications are not enclosed pursuant

to the waiver of 37 CFR 1.98 (a)(2)(i) for all applications filed after June 30, 2003.

03/30/2006 WABDELRI 00000045 024377 10525288

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This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that the listed documents are material or constitute "prior art." If the Examiner applies the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of the documents.

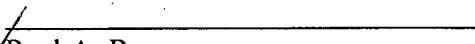
Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should the documents be applied against the claims of the present application.

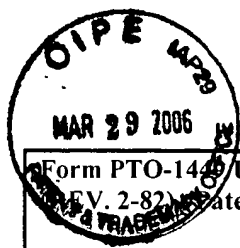
Applicants have enclosed the required fee of \$180.00 due in connection with this. If any additional fee is due, or if any overpayment has been made, the Commissioner is authorized to charge any such fee or credit any overpayment, to our Deposit Account No. 02-4377.

Respectfully submitted,

BAKER BOTTS L.L.P.



By:   
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<b>Form PTO-1449</b> U.S. Department of Commerce Patent and Trademark Office  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)	Atty. Docket No. A35760-PCT-USA (070050.2713)	Serial No. 10/525,288
	Applicant James S. Im	
	Filing Date 02/16/2005	Group 2813
	Examiner	

**U.S. PATENT DOCUMENTS**

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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					Yes No
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					Yes	No
	113.	9931719	06/24/1999	WO		<u>No</u>
	114.	0014784	03/16/2000	WO		
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					Yes	No
	129.	04017380	02/26/2004	WO		
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	156.	Yoshimoto, et al., "Excimer-Laser-Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", p. 285-286, AM-LCD 2000. No month.
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\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.